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FIG. 1

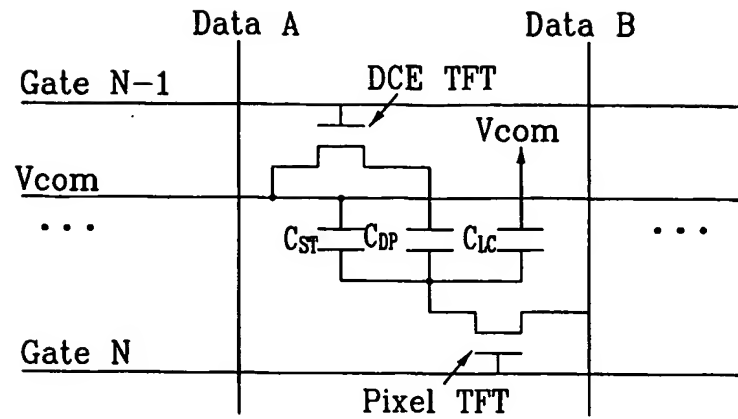




FIG. 2B

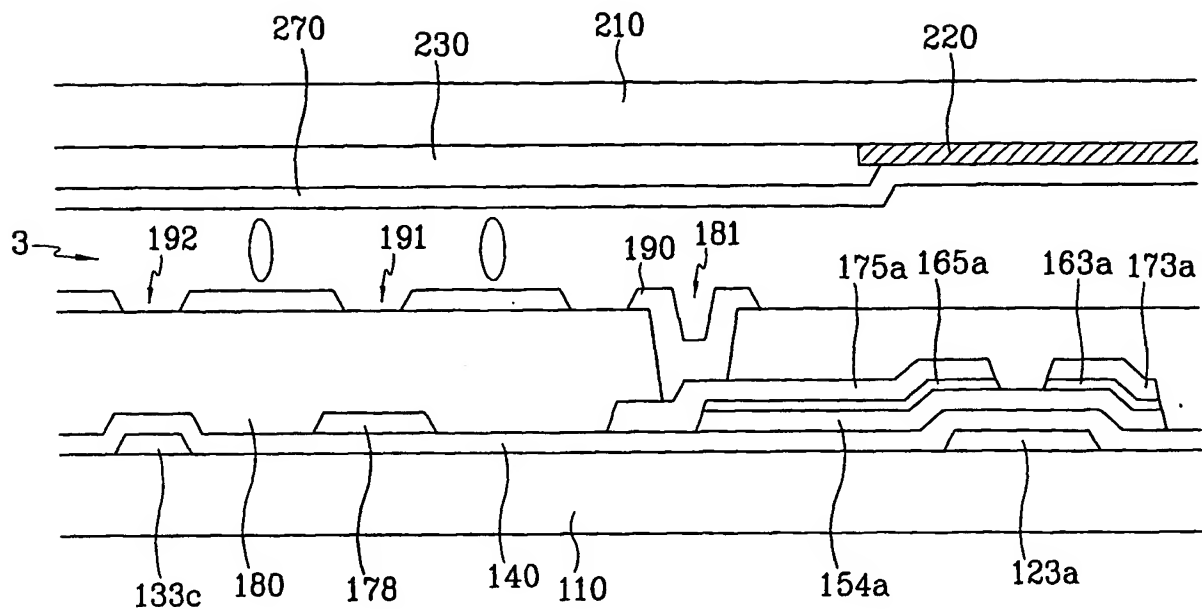


FIG. 2C

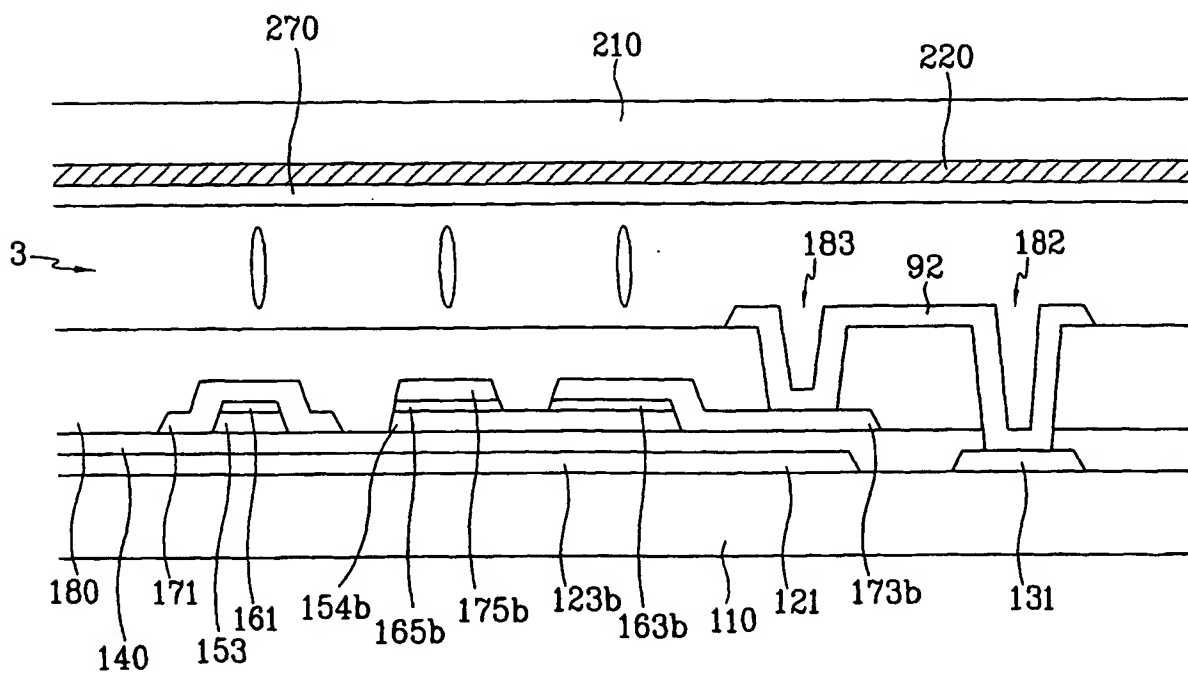
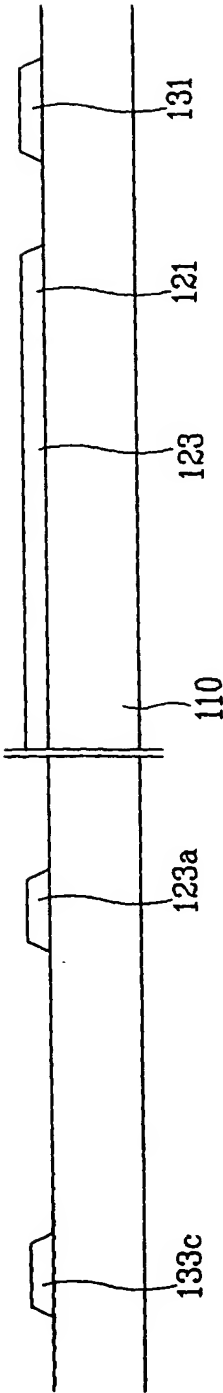
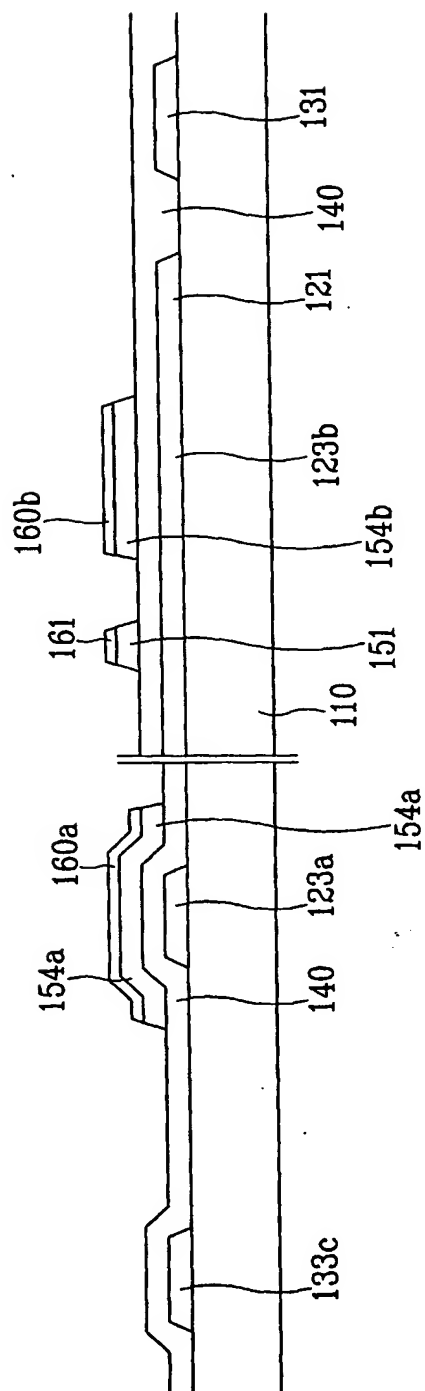


FIG. 3A



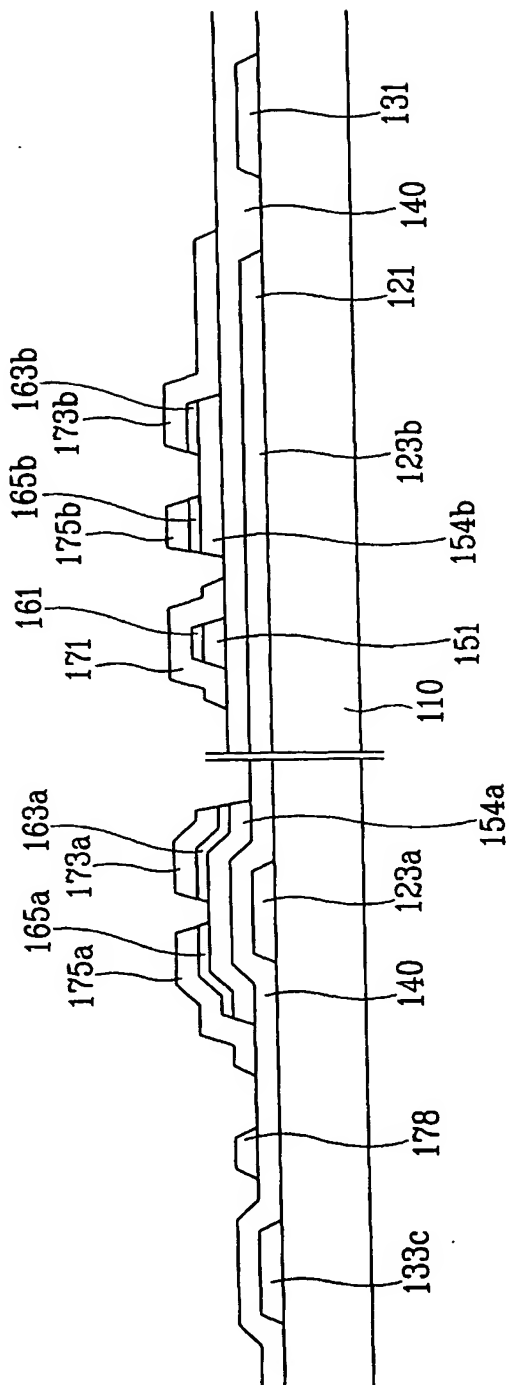
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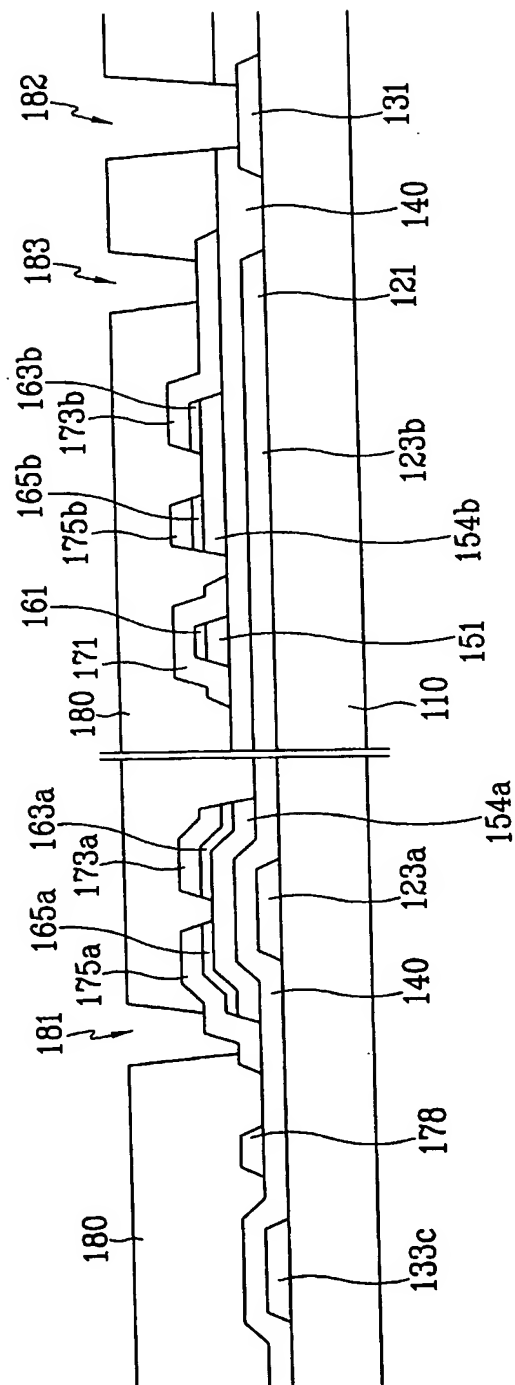
FIG. 3B



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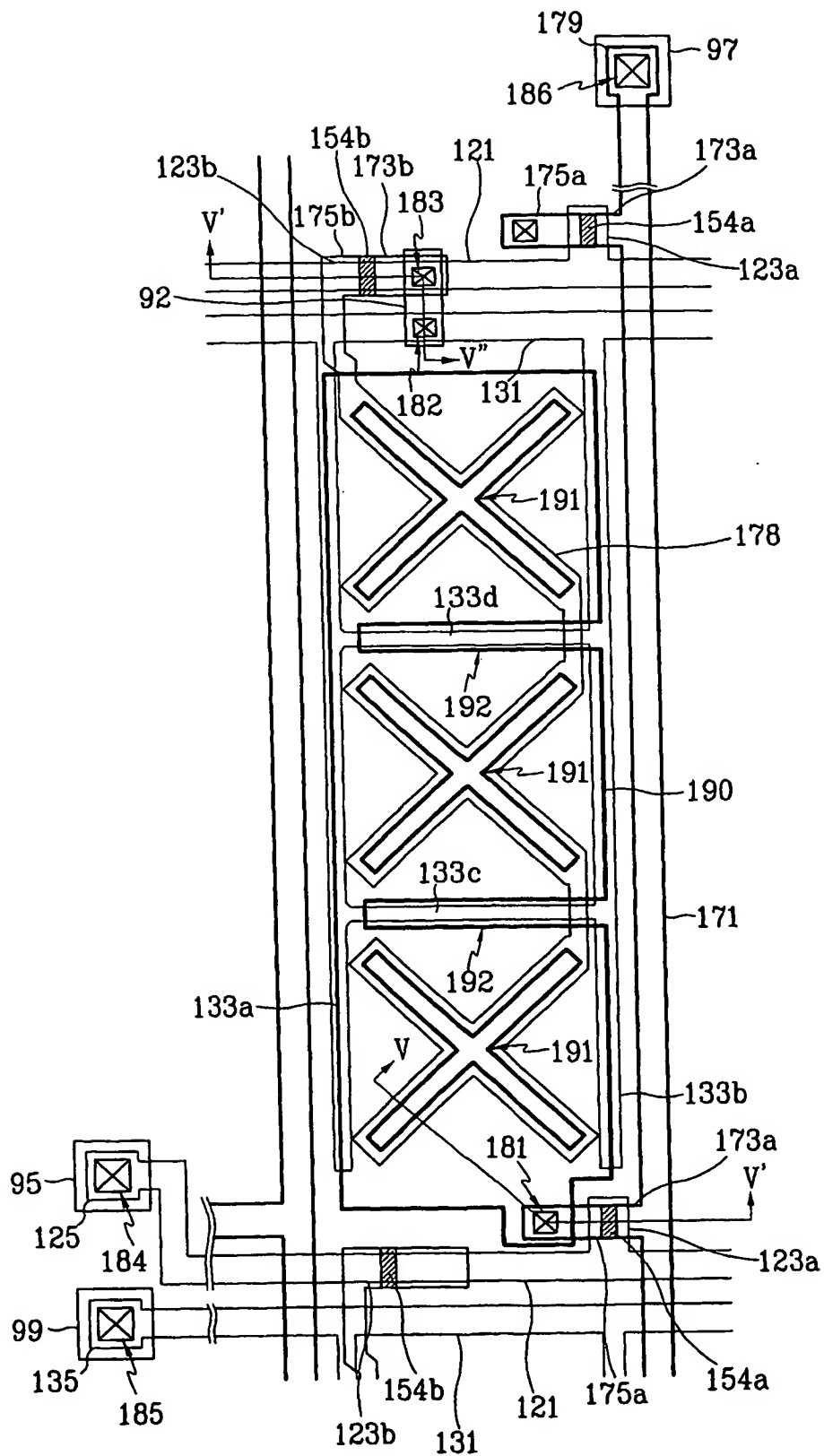
FIG. 3C





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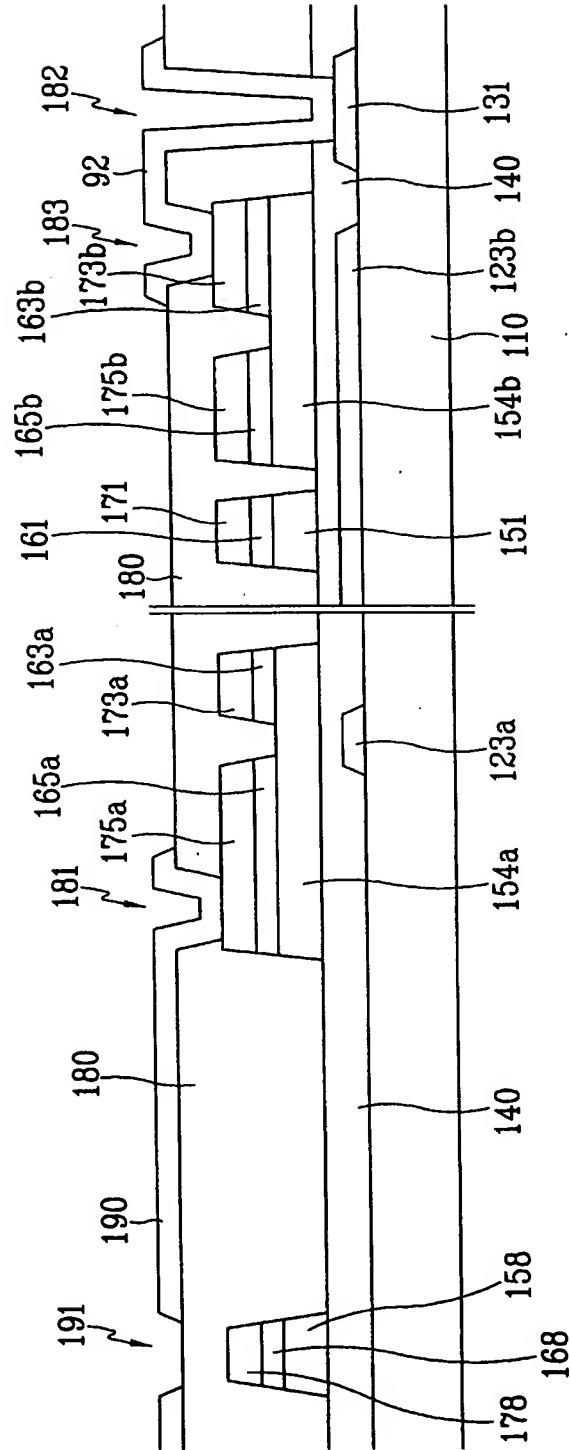
FIG. 4





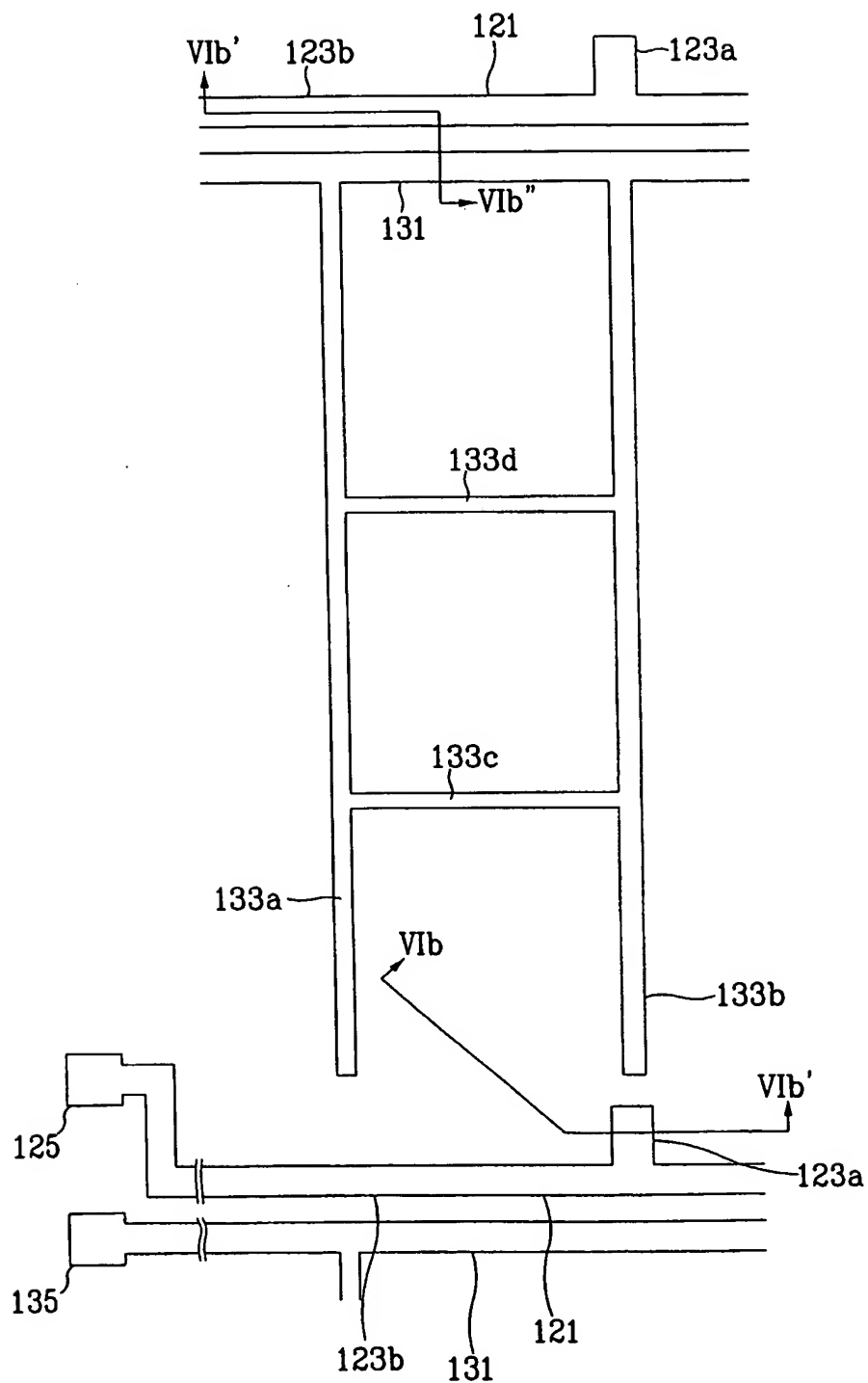
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FIG. 5



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FIG. 6A







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FIG. 8A

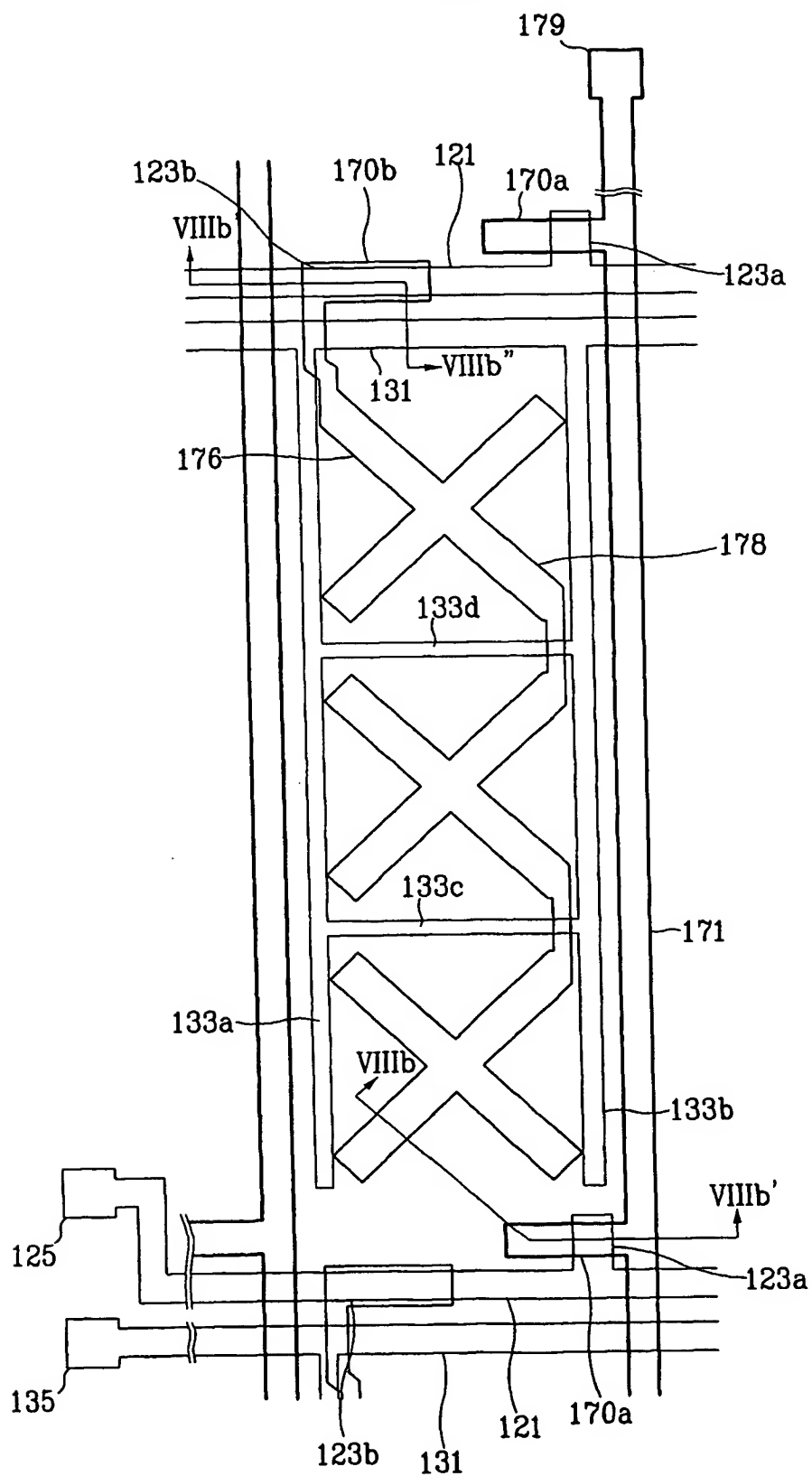


FIG. 8B

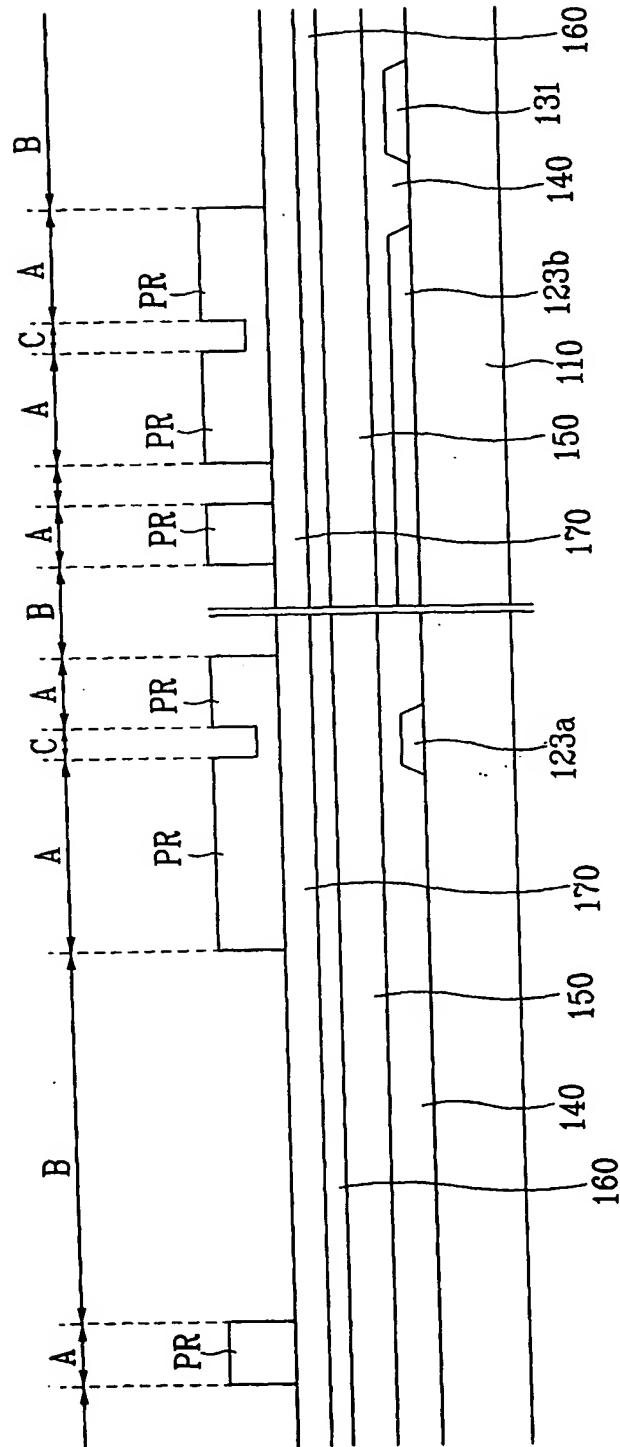
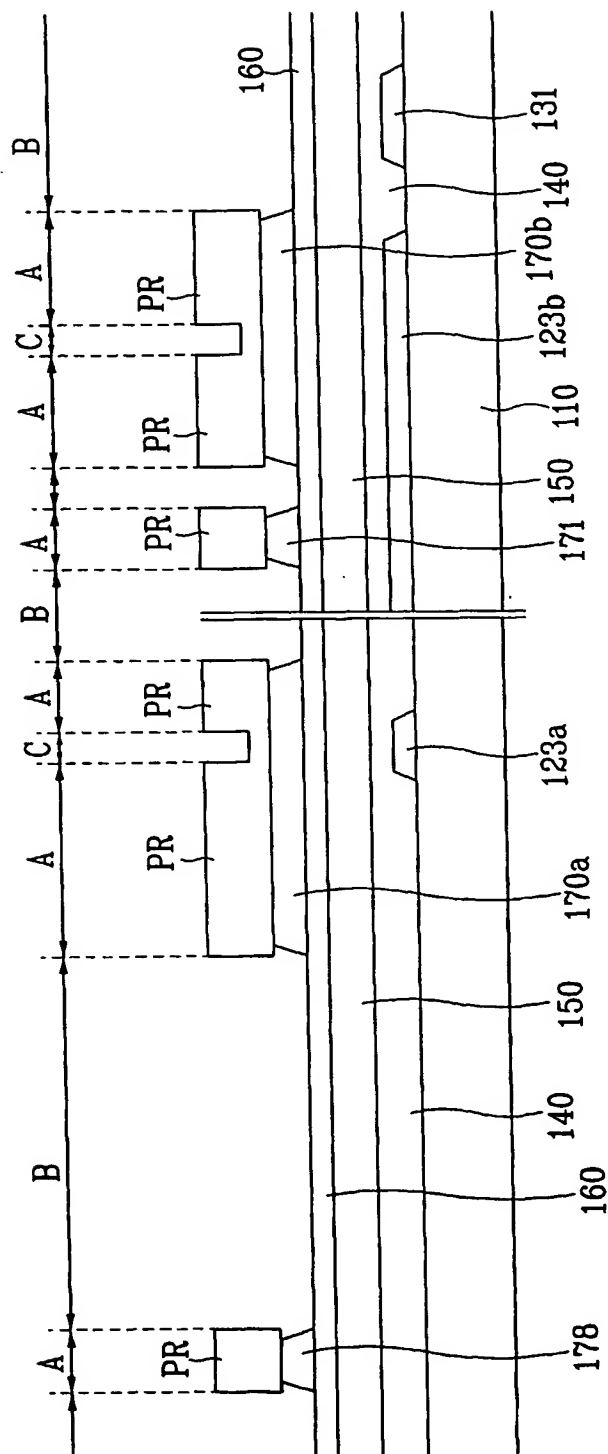


FIG. 9



This cross-sectional view shows a semiconductor device with a substrate 131. A layer 140 is formed on the substrate. A series of layers 144, 151, 154a, and 154b are stacked. A layer 160a is formed on the substrate, and a layer 160b is formed on the substrate. A layer 161 is formed on the substrate. A layer 168 is formed on the substrate. A layer 170a is formed on the substrate, and a layer 170b is formed on the substrate. A layer 171 is formed on the substrate. A layer 178 is formed on the substrate. A layer 180 is formed on the substrate.



FIG. 11A

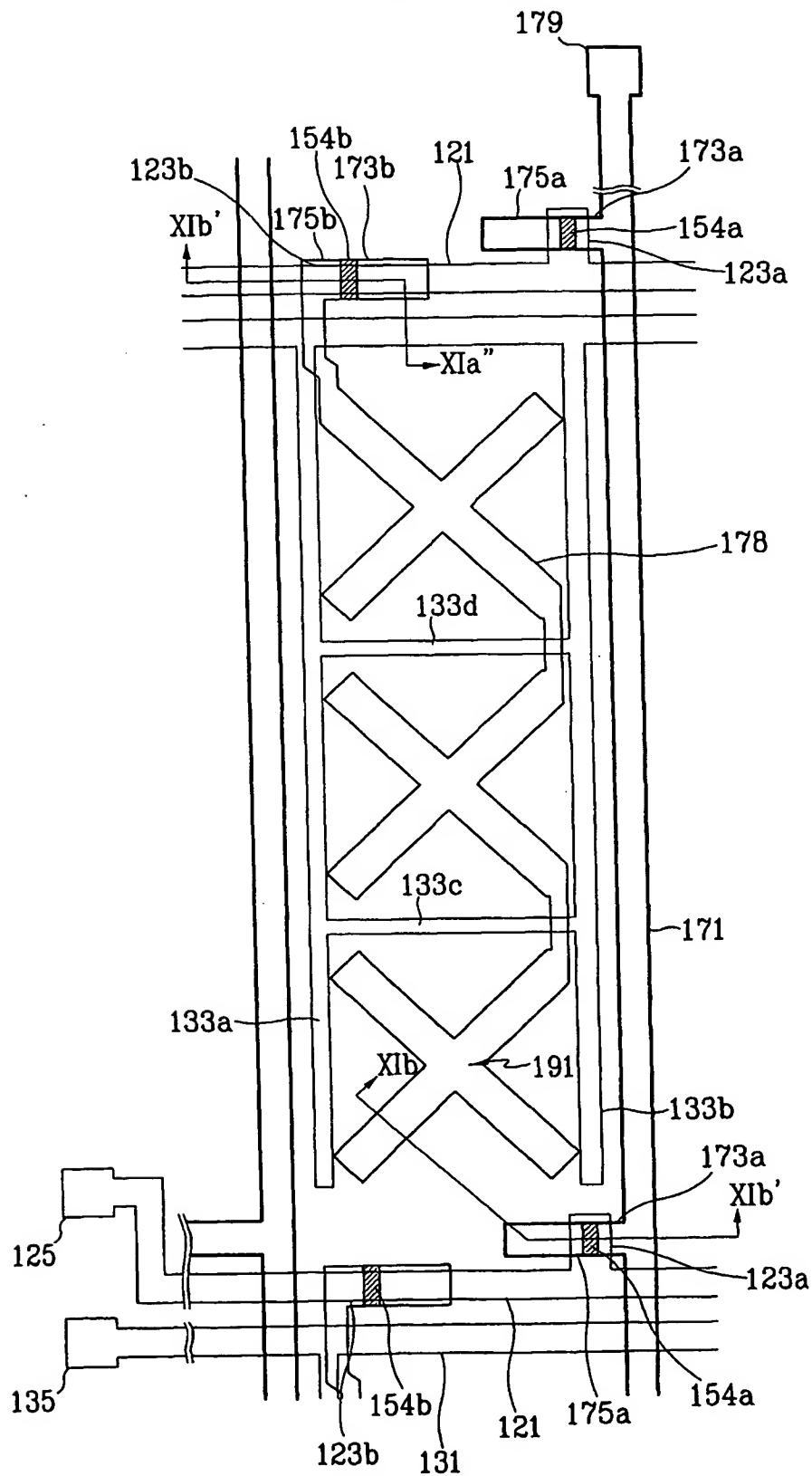
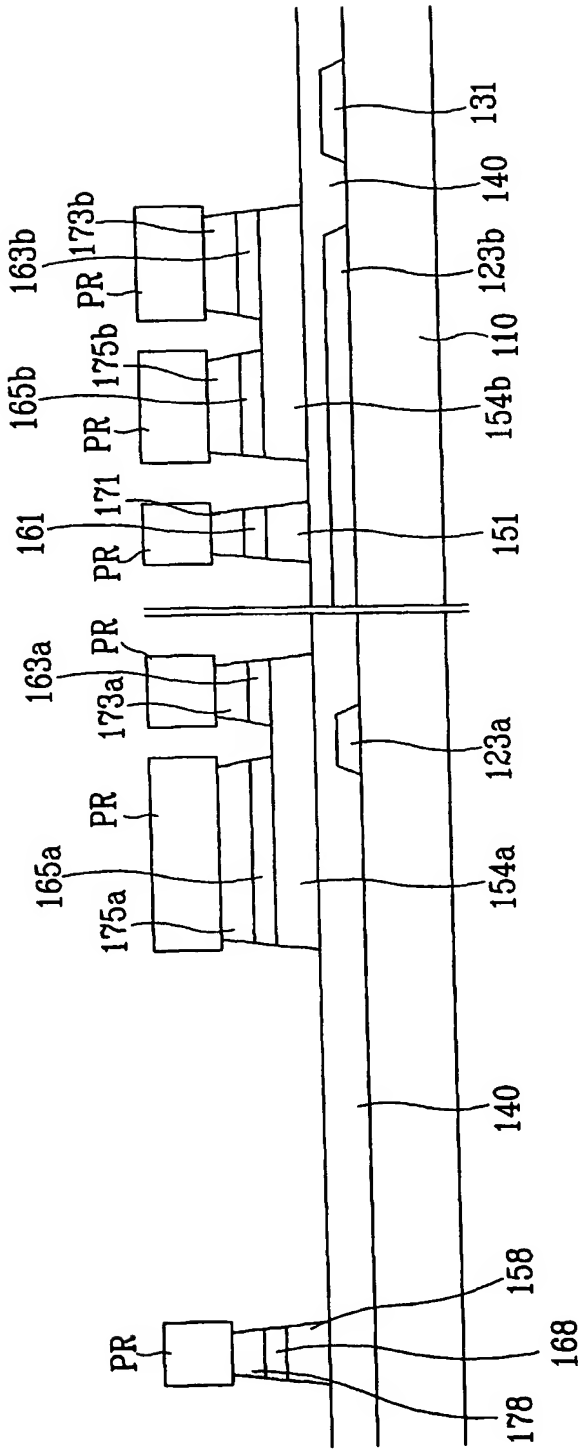


FIG. 11B



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FIG. 12

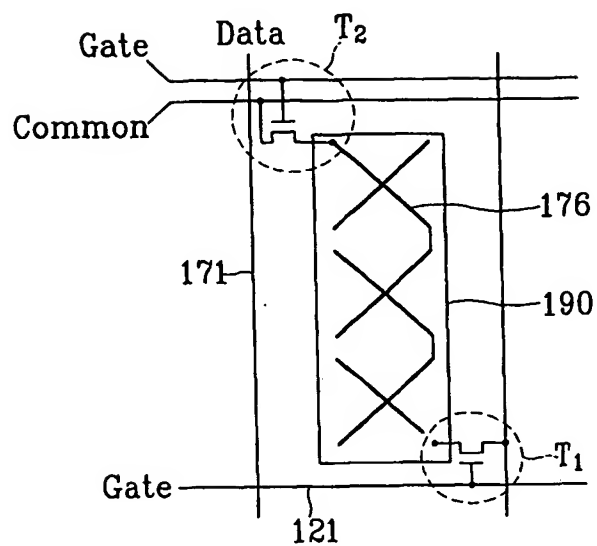
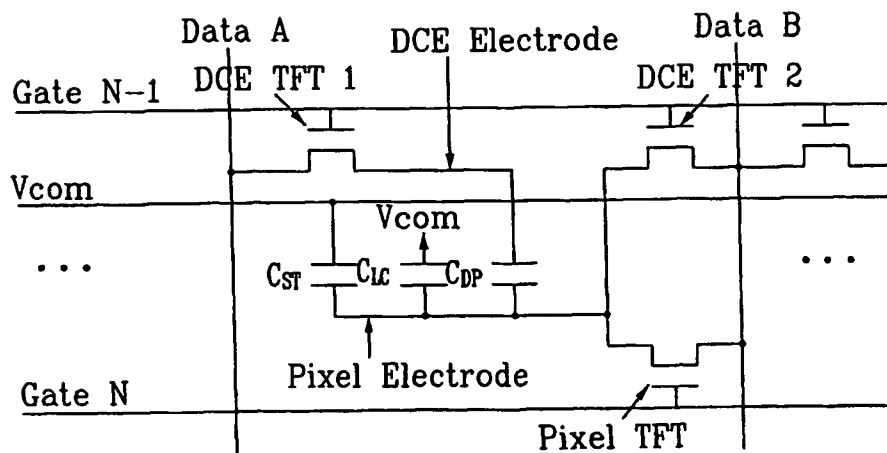


FIG. 13



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FIG. 14

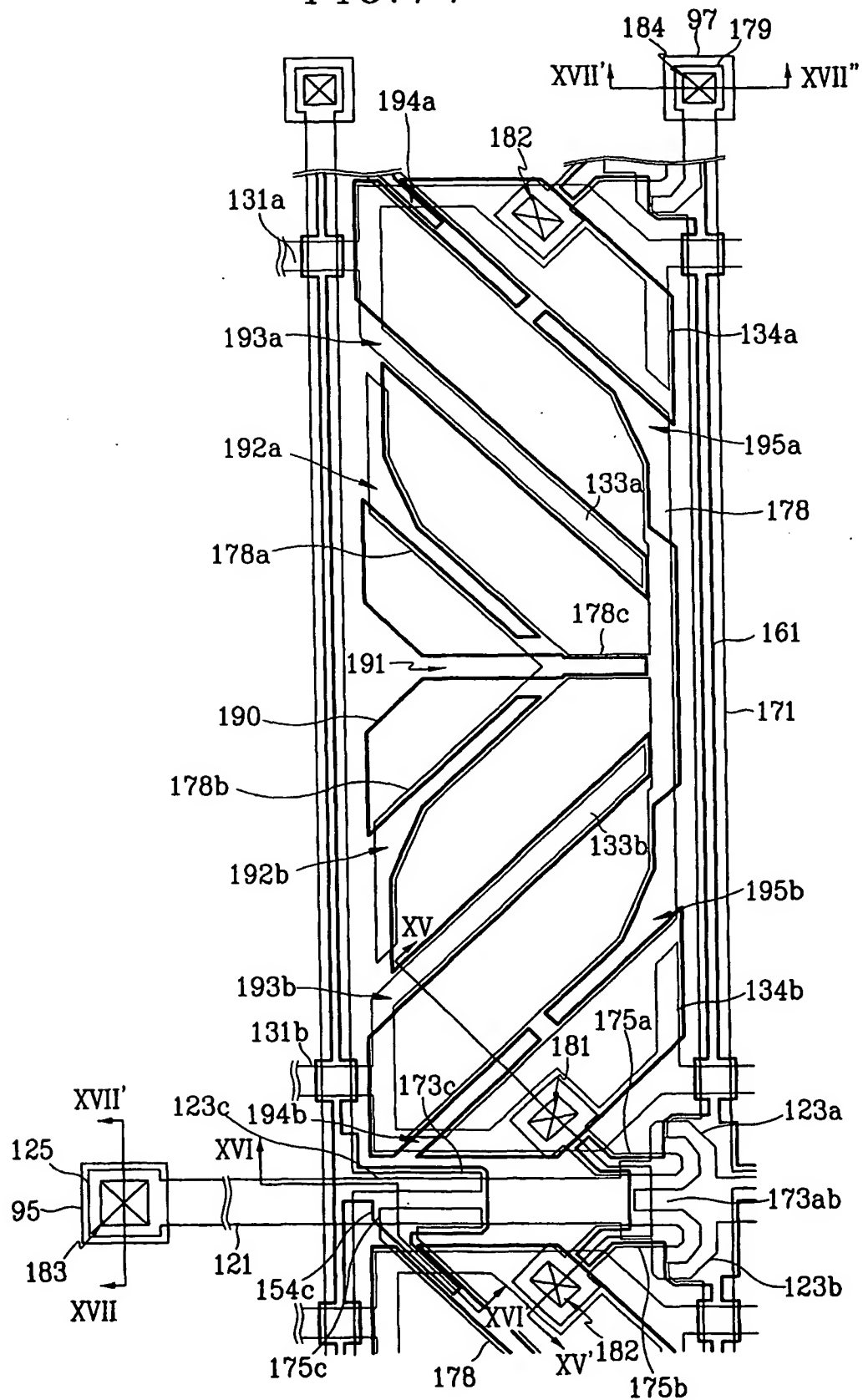


FIG. 15

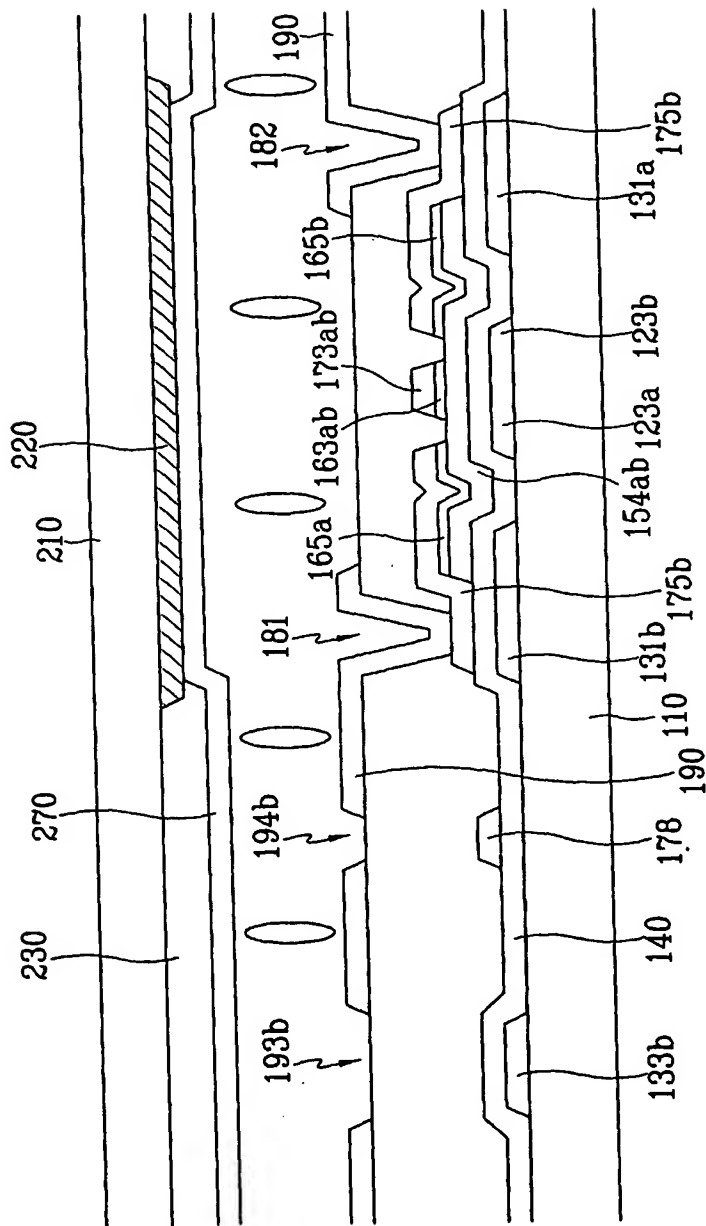


FIG. 16

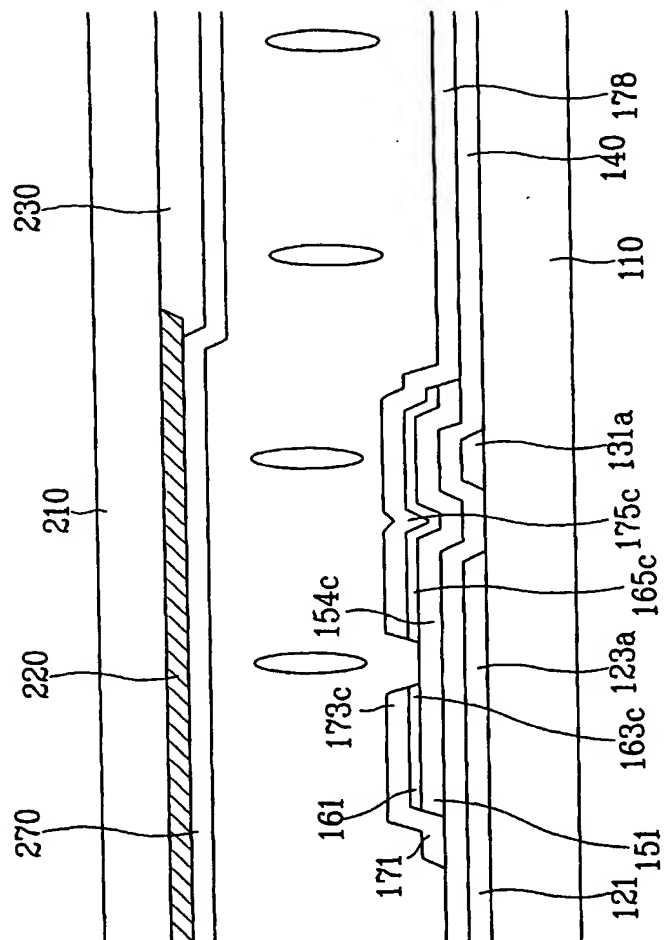


FIG. 17

